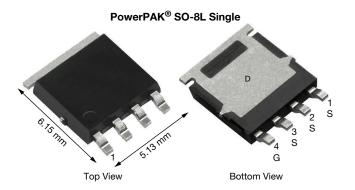
SQJ407EP

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Vishay Siliconix

Automotive P-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	-30
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.0044
$R_{DS(on)}$ (Ω) at V_{GS} = -4.5 V	0.0071
I _D (A)	-60
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

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KONS COMPLIANT HALOGEN

	IGS (T _C = 25 °C, unless				
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-30	V	
Gate-source voltage		V _{GS}	± 20		
Continuous drein surrent	T _C = 25 °C ª	1	-60		
Continuous drain current	T _C = 125 °C	ID	-56		
Continuous source current (diode conduc	Is	-60	А		
Pulsed drain current ^b		I _{DM}	-155		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-41		
Single pulse avalanche energy		E _{AS}	84	mJ	
Maximum power dissipation ^b	T _C = 25 °C	D	68	W	
	T _C = 125 °C	P _D	22		
Operating junction and storage temperation	T _J , T _{stg}	-55 to +175	*0		
Soldering recommendations (peak temperature) ^{d, e}		0	260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	68	°C/W
Junction-to-case (drain)		R _{thJC}	2.2	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = -250 μΑ	-30	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V_{GS} , I_D = -250 μ A	-1.5	-2.0	-2.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	-50	μA
		$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	-200	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge -5 V$	-30	-	-	А
		V _{GS} = -10 V	I _D = -10 A	-	0.0036	0.0044	
Durin anuma an atata nasistana a	P	V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0060	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -10 \text{ V}$	I _D = -10 A, T _J = 175 °C	-	-	0.0068	Ω
		V _{GS} = -4.5 V	I _D = -6 A	-	0.0059	0.0071	
Forward transconductance b	9 _{fs}	V _{DS} =	-15 V, I _D = -10 A	-	60	-	S
Dynamic ^b					•	•	
Input capacitance	C _{iss}			-	8200	10 700	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = -25 V, f = 1 MHz	-	950	1300	pF
Reverse transfer capacitance	C _{rss}			-	785	1050	
Total gate charge ^c	Qg			-	169	260	
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	24	-	nC
Gate-drain charge ^c	Q _{gd}			-	32	-	
Gate resistance	Rg		f = 1 MHz	0.5	1.05	1.6	Ω
Turn-on delay time ^c	t _{d(on)}			-	23	35	
Rise time ^c	t _r	$\label{eq:V_DD} \begin{array}{l} V_{\text{DD}} = -15 \text{ V}, \ R_{\text{L}} = 3 \ \Omega \\ I_{\text{D}} \cong -5 \ A, \ V_{\text{GEN}} = -10 \ V, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	19	30	- ns
Turn-off delay time ^c	t _{d(off)}			-	72	120	
Fall time ^c	t _f			-	14	25	
Source-Drain Diode Ratings and Charac	teristics ^b						1
Pulsed current ^a	I _{SM}				-	-155	А
Forward voltage	V _{SD}	I _F = -10 A, V _{GS} = 0 V		-	-0.75	-1.2	V
Body diode reverse recovery time	t _{rr}			-	39	90	ns
Body diode reverse recovery charge	Q _{rr}	1		-	45	100	nC
Reverse recovery fall time	t _a	- I _F = 10 A, di/dt = 100 A/μs		-	22	-	
Reverse recovery rise time	t _b	1		-	19	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			_	-2.3	_	А

Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%.$

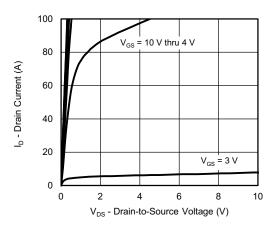
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

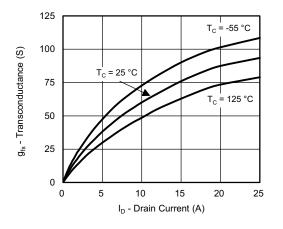
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



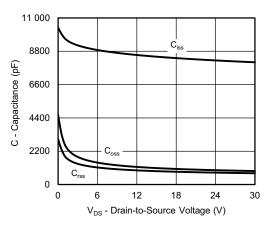
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



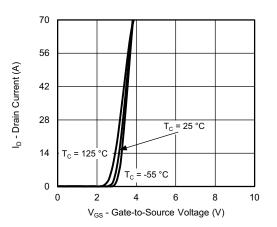
Output Characteristics



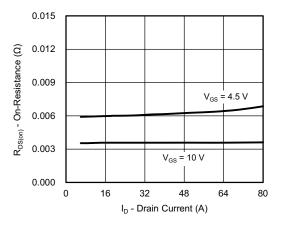
Transconductance



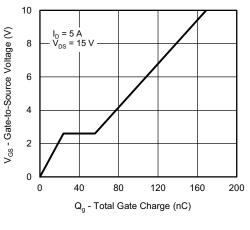
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

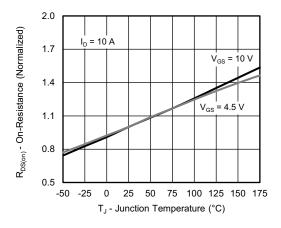
S16-2657-Rev. A, 02-Jan-17

3 tions, contact: automostechsur Document Number: 62806

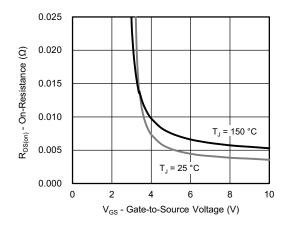
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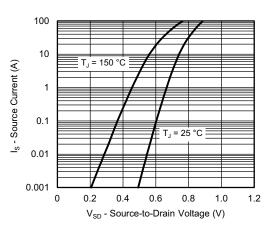
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



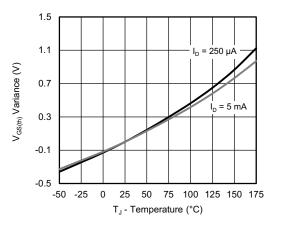
On-Resistance vs. Junction Temperature



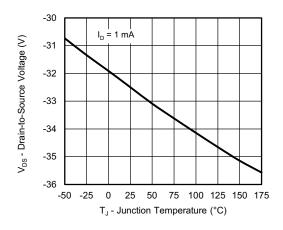
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Threshold Voltage

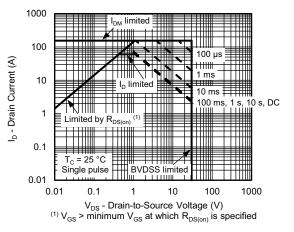


Drain-Source Breakdown vs. Junction Temperature

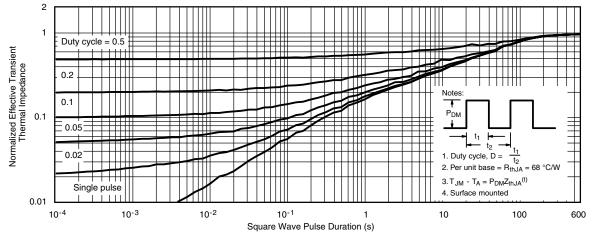
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THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Safe Operating Area

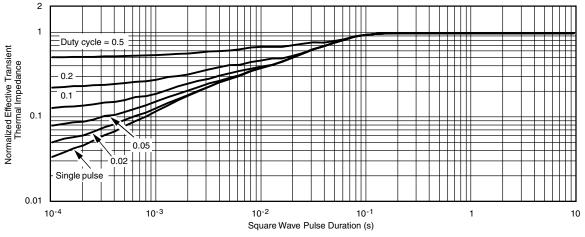


Normalized Thermal Transient Impedance, Junction-to-Ambient



Document Number: 62806

THERMAL RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

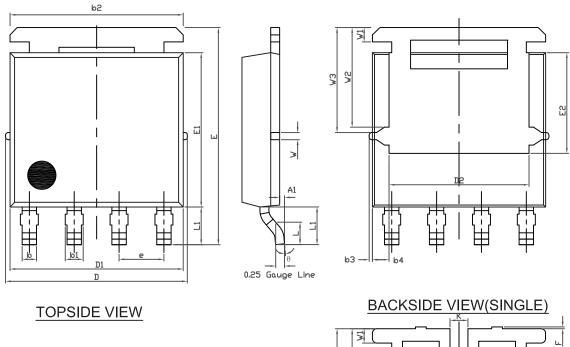
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

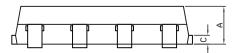
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

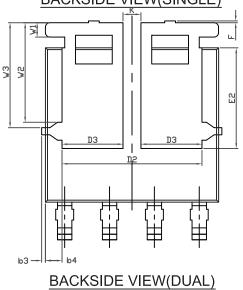
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PowerPAK[®] SO-8L Case Outline 2







Package Information



Vishay Siliconix

DIM.		MILLIMETERS			INCHES			
DINI.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC			0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51			0.020			
W	0.23			0.009				
W1	0.41			0.016				
W2	2.82			0.111				
W3		2.96			0.117			
q	0°	-	10°	0°	-	10°		

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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